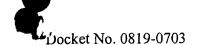
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IN THE UNITED STATES IN TENT AND TRADEMARK OFFICE

Art Unit: Unassigned In re Patent Application of) Examiner: Unassigned Yoshiaki HASEGAWA et al. Serial No. 09/993,771 CERTIFICATE OF MAILING Filed: November 27, 2001 I hereby certify that this correspondence is being deposited with The United States Postal Service with sufficient postage as First For: METHOD FOR MANUFACTURING) Class Mail in an envelope addressed to Complissioner for Patents, Washington, D.C. 20231, on SEMICONDUCTOR AND METHOD) FOR MANUFACTURING SEMICONDUCTOR DEVICE

PRELIMINARY AMENDMENT

Honorable Commissioner of Patents

Washington, D.C. 20231

Sir:

Please preliminarily amend the above identified patent application as follows:

IN THE SPECIFICATION:

Please amend the specification as follows:

On Page 27, First Full Paragraph

Thus, according to the second variation, the etching stop layer 19C having a super lattice structure is formed under the p-type second cladding layer 20 to be etched, whereby it is possible to control the thickness (remaining thickness) of the p-type first cladding layer 18 with a high precision. As a result, it is possible to obtain a desired thickness, i.e., an optimal value, for the thickness of the p-type first cladding layer 18. Therefore, the light confinement efficiency in the MQW active layer 15 is significant improved. This is because of the prevention of an etching damage to the MQW active layer 15.

On Page 30, Fourth Paragraph continuing on Page 31

As illustrated in FIG. 10, during the etching process on the p-type second cladding layer 20, which is made of p-type Al_{0.07}Ga_{0.93}N, the wavelength of the detected PL light is about 350

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